

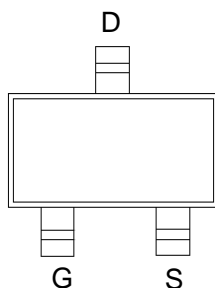
20V/0.9A N-Channel MOSFET

Features

- TrenchFET Power MOSFET
- Low Gate Charge
- Low On-resistance
- Surface Mount Package

Application

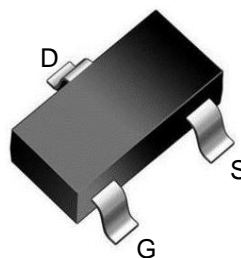
- Battery protection
- Load switch
- Power management



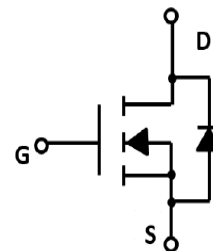
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
20V	220mΩ@4.5V	0.9A
	300mΩ@2.5V	



SOT-23 top view



Schematic diagram

Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage		20	V
V_{GS}	Gate-Source Voltage		±12	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$	0.9	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$	2.0	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	0.9	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	0.35	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		357	°C/W

Electrical Characteristics (T_J=25 °C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25 °C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	VGS=0V, ID=250µA	20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	VDS=16V, VGS=0V	--	--	1	µA
I _{GSS}	Gate-Body Leakage Current	VGS=±12V, VDS=0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	VDS=VGS, ID=250µA	0.6	1.0	1.5	V
R _{DS(on)}	Drain-Source On-State Resistance	VGS=4.5V, ID=0.9A	--	170	220	mΩ
		VGS=2.5V, ID=0.7A	--	270	350	mΩ
Dynamic Electrical Characteristics @ T_J = 25 °C (unless otherwise stated)						
C _{ISS}	Input Capacitance	VDS=10V, VGS=0V, f=1MHz	--	83	--	pF
C _{OSS}	Output Capacitance		--	21	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	10.2	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	VDS=10V, ID=0.5A, VGS=4.5V	--	0.8	--	nC
Q _{gs}	Gate Source Charge		--	0.1	--	nC
Q _{gd}	Gate Drain Charge		--	0.2	--	nC
t _{d(on)}	Turn-on Delay Time	VDD=10V, ID=0.5A, VGS=4.5V, RG=3Ω	--	7	--	nS
t _r	Turn-on Rise Time		--	10	--	nS
t _{d(off)}	Turn-Off Delay Time		--	35	--	nS
t _f	Turn-Off Fall Time		--	15	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25 °C, I _S =0.3A,	--	0.8	1.2	V

Typical Operating Characteristics

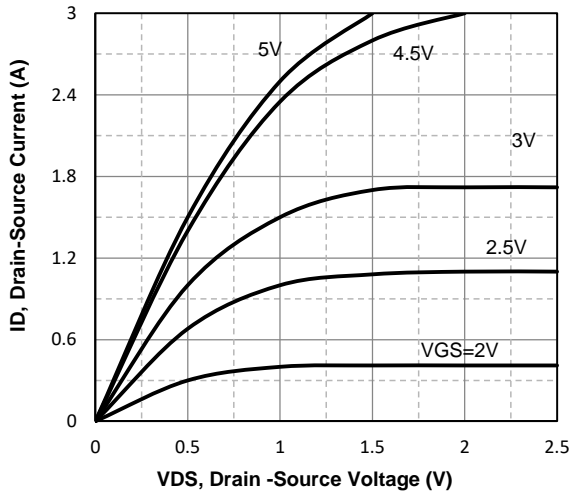


Fig1. Typical Output Characteristics

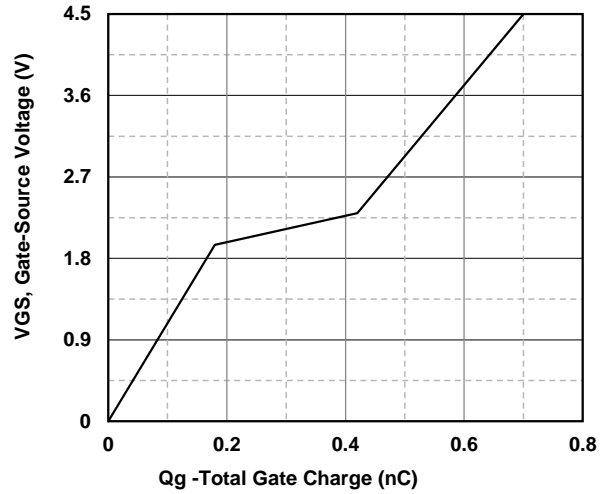


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

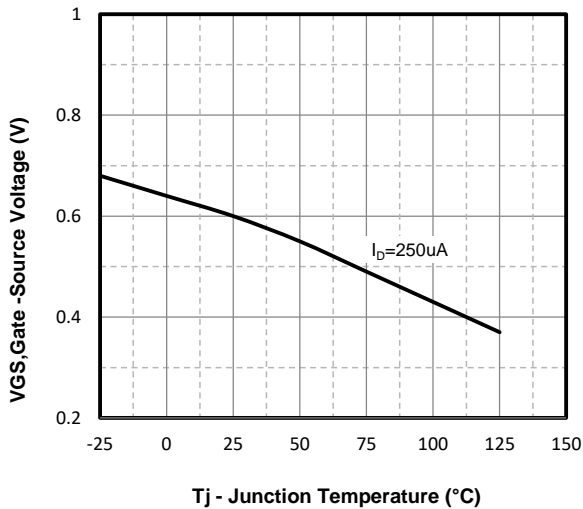


Fig3. Normalized Threshold Voltage Vs. Temperature

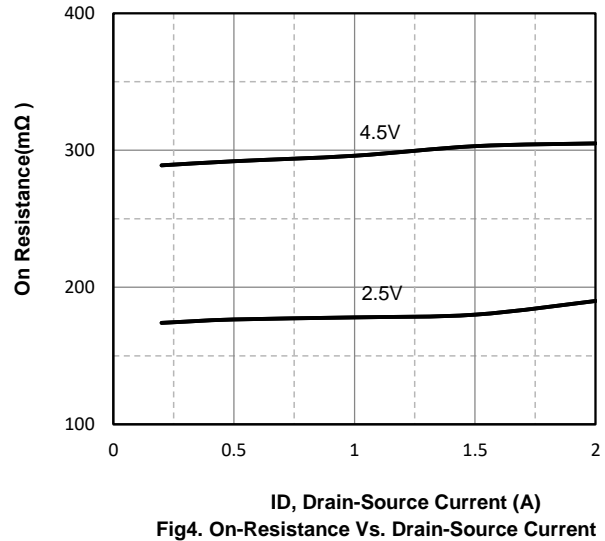


Fig4. On-Resistance Vs. Drain-Source Current

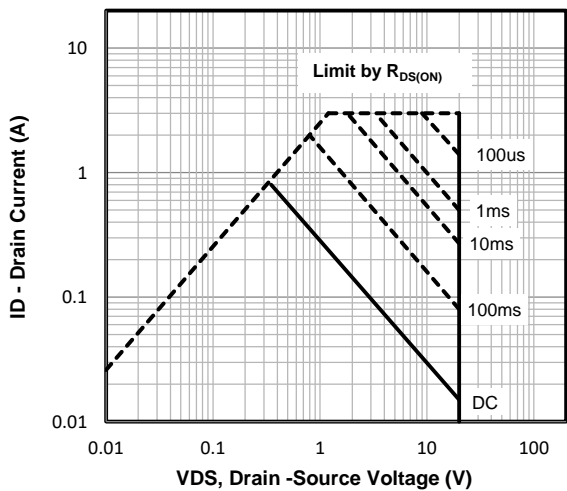


Fig5. Maximum Safe Operating Area

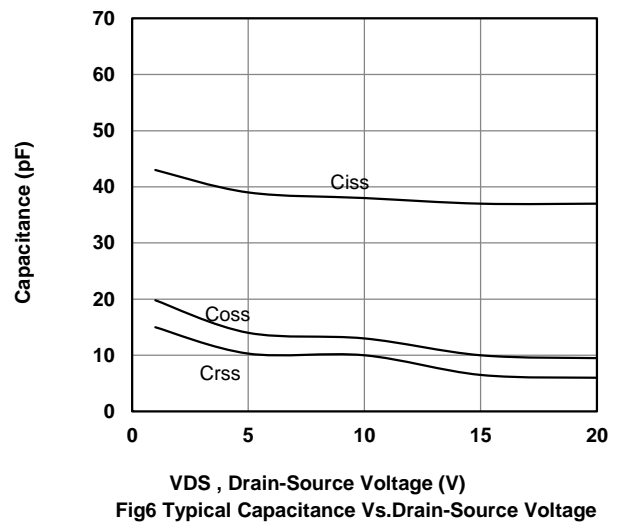
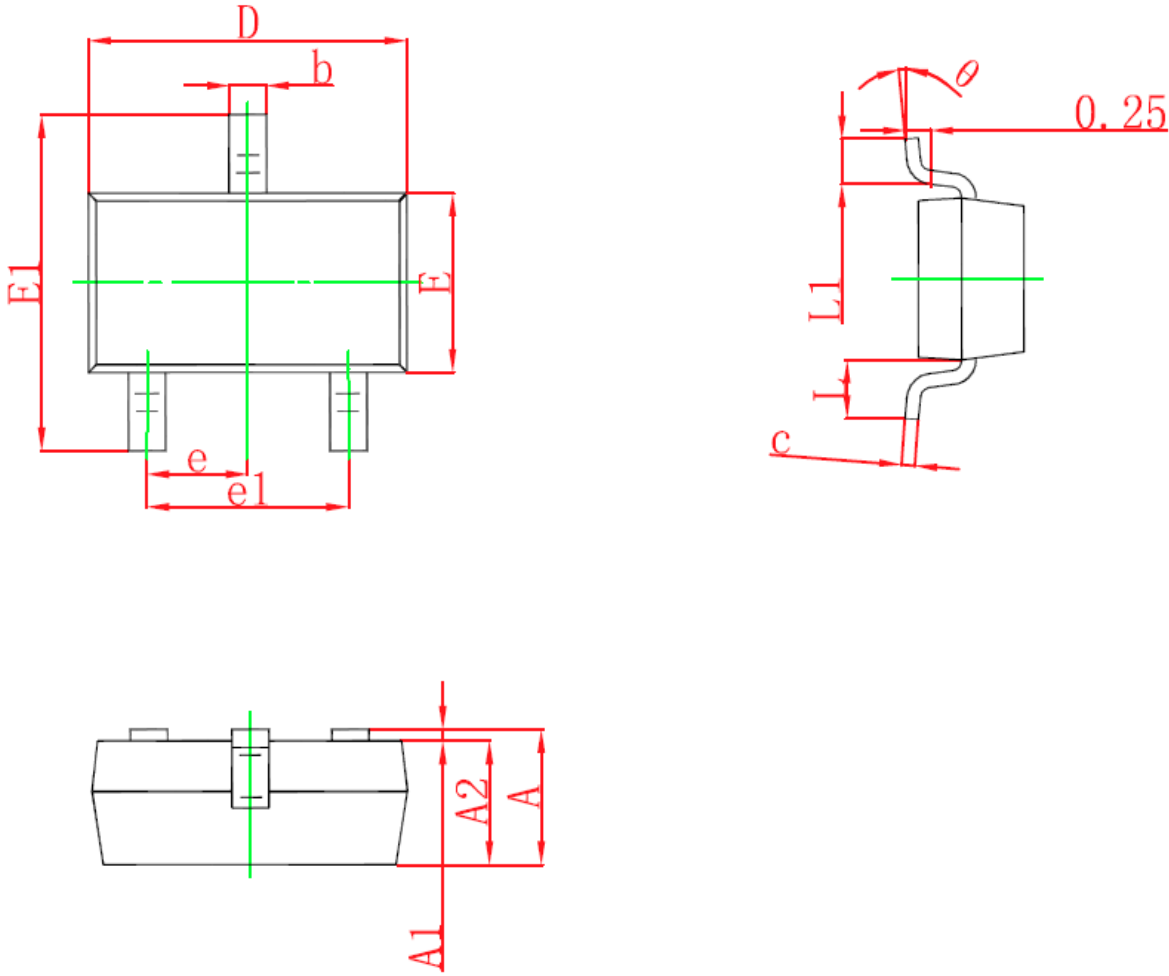


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-23 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°